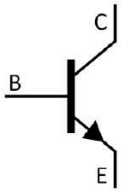
Silicon NPN transistor in a TO-92 Plastic Package.

Complementary pair with KSB564A

Audio frequency power amplifier.

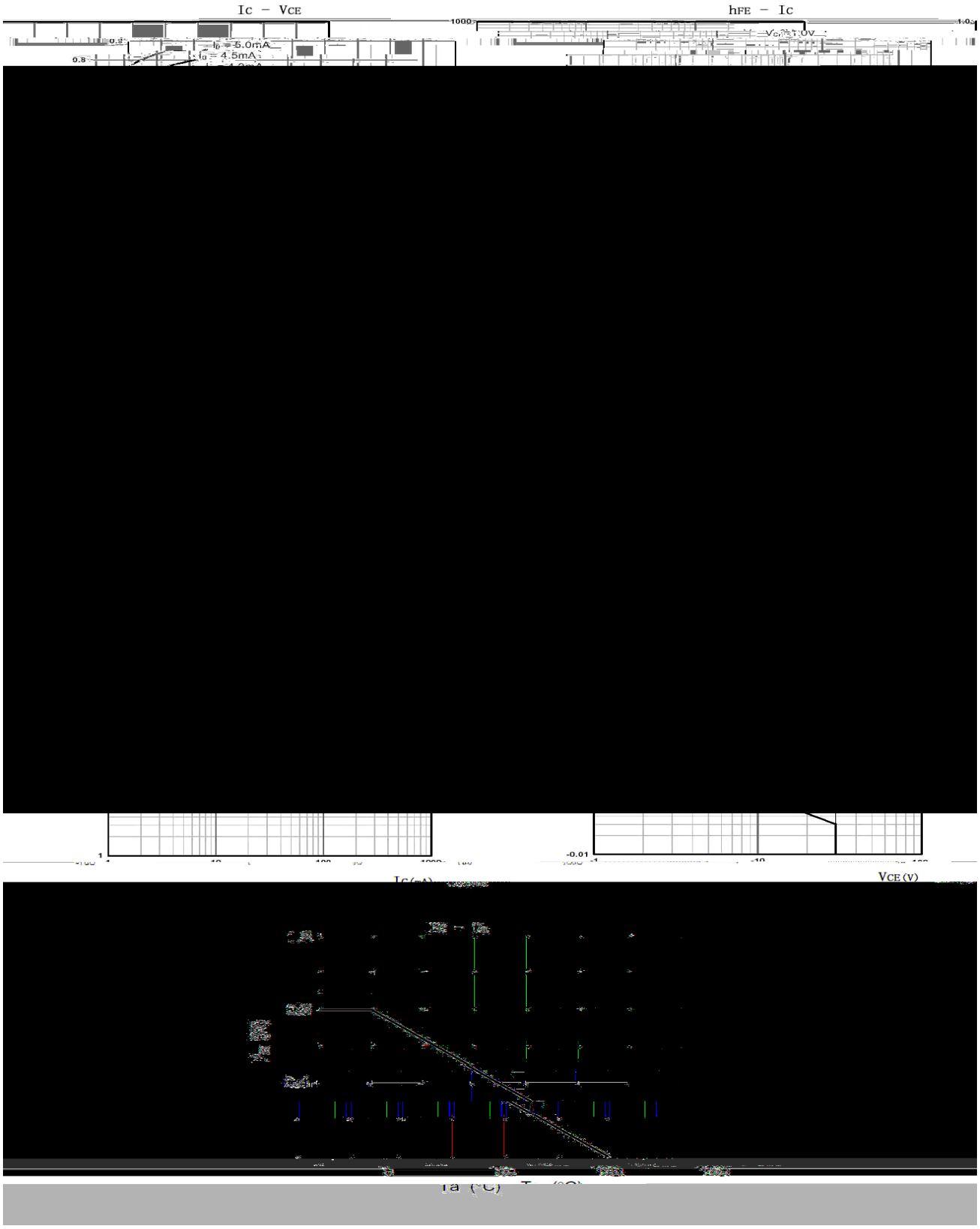


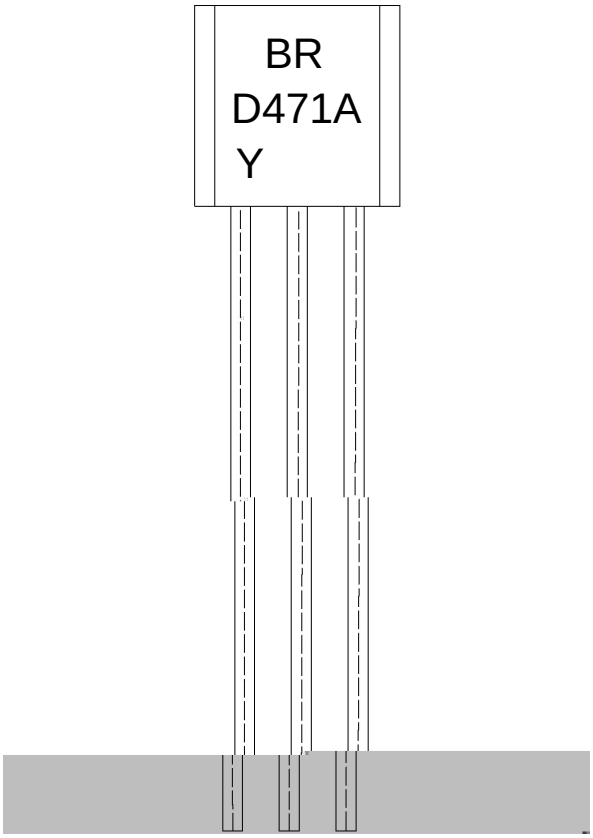


PIN1 Collector PIN 2 Base PIN 3

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=1.0V I_C=100mA	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1.0A I_B=0.1A			0.5	V
Base -Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=1.0A I_B=0.1A			1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}=6.0V I_C=10mA		130		MHz
Output Capacitance	C_{ob}	V_{CB}=6.0V I_E=0 f=1.0MHz		16		pF


Ic – VCE
hFE – Ic
IB = 5.0mA
IB = 4.5mA
VCE (V)
Ta (°C)



Note:

BR:	Company Code.
D471A:	Product Type.
Y:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

Note:

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension	(unit mm3)